NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **ASI 2SC2951** is a High Frequency Transistor Designed for General Purpose Oscillator Applications up to 10 GHz.

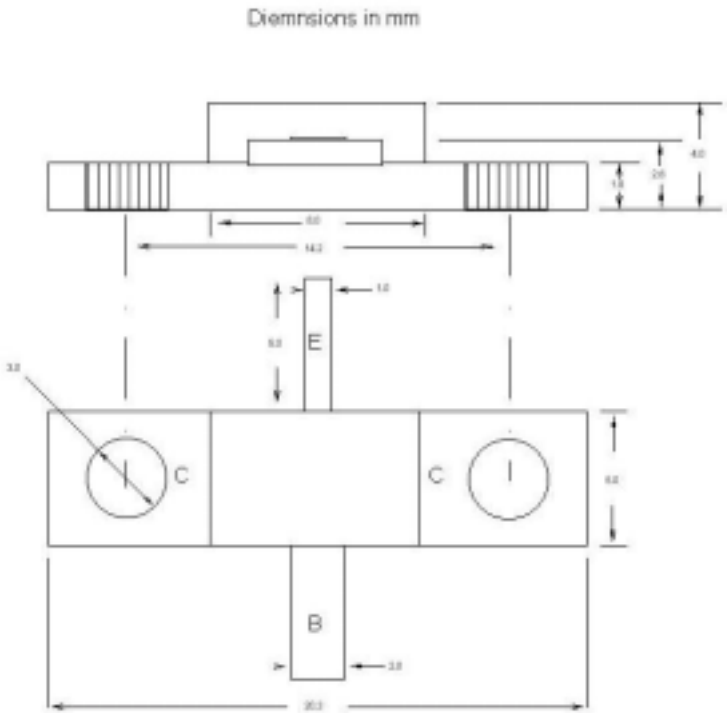
FEATURES:

- **P_{OSC}** = 630 mW Typical at 7.5 GHz
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	440 mA
V_{CE}	16 V
V_{CB}	25 V
P_{DISS}	9.7 W @ T_C = 25 °C
T_J	-65 to +200 °C
T_{STG}	-65 to +200 °C
θ_{JC}	18 °C/W

PACKAGE STYLE .200 2L FLG



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 1.0 mA	16			V
BV_{CBO}	I_C = 100 µA	25			V
BV_{EBO}	I_E = 100 µA	1.5			V
I_{CBO}	V_{CB} = 15 V			1.0	µA
I_{EBO}	V_{EB} = 1.0 V			4.0	µA
h_{FE}	V_{CE} = 8.0 V I_C = 200 mA	20		200	---
C_{OB}	V_{CB} = 10 V f = 1.0 MHz		2.9	4.0	pF
$\lvert S21 \rvert^2$	V_{CC} = 8.0 V I_C = 200 mA f = 1.0 GHz	3.5			dB
P_{OSC}	V_{CE} = 12 V I_C = 200 mA f = 7.5 GHz		630		mW

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Specifications are subject to change without notice.